

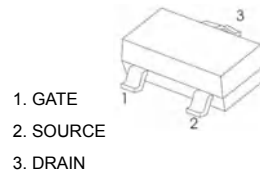
FEATURES

- * High density cell design for low $R_{DS(ON)}$
- * Voltage controlled small signal switch
- * Rugged and reliable
- * High saturation current capability

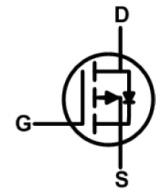
V_{DSS} -20 V
 I_D -2.3 A
 $R_{DS(ON)}$ 90 m Ω

A1SHB.

SOT-23



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current	I_D	-2.3	A
Pulsed Drain Current	I_{DM}	-10	
Continuous Source-Drain Diode Current	I_S	-0.72	
Maximum Power Dissipation	P_D	1.0	W
Thermal Resistance from Junction to Ambient($t \leq 5s$)	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4		-1	
Gate-source leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -2.8A$		0.090	0.112	Ω
		$V_{GS} = -2.5V, I_D = -2.0A$		0.110	0.142	
Forward transconductance ^a	g_{fs}	$V_{DS} = -5V, I_D = -2.8A$		6.5		S
Dynamic^b						
Input capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		405		pF
Output capacitance	C_{oss}			75		
Reverse transfer capacitance	C_{rss}			55		
Total gate charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -3A$		5.5	10	nC
		$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -3A$		3.3	6	
Gate-source charge	Q_{gs}	$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -3A$		0.7		
Gate-drain charge	Q_{gd}			1.3		
Gate resistance	R_g	$f = 1MHz$		6.0		Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10V,$ $R_L = 10\Omega, I_D = -1A,$ $V_{GEN} = -4.5V, R_g = 1\Omega$		11	20	ns
Rise time	t_r			35	60	
Turn-off delay time	$t_{d(off)}$			30	50	
Fall time	t_f			10	20	
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^\circ\text{C}$			-1.3	A
Pulse diode forward current ^a	I_{SM}				-10	
Body diode voltage	V_{SD}	$I_S = -0.7A$		-0.8	-1.2	V

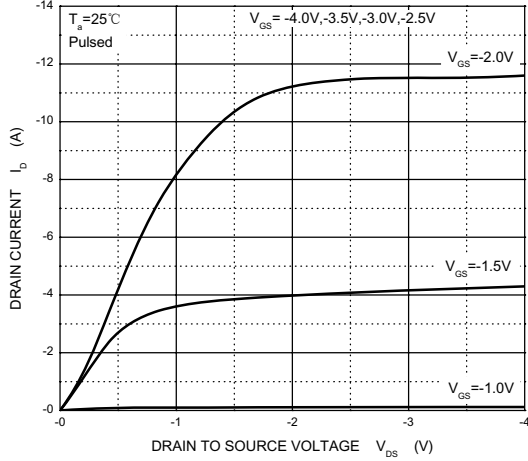
Notes :

a. Pulse Test : Pulse Width < 300 μs , Duty Cycle $\leq 2\%$.

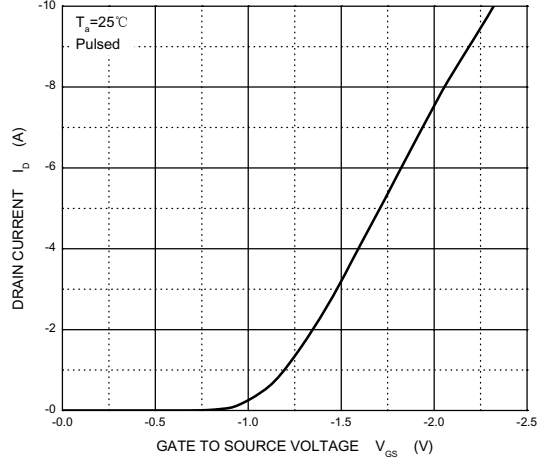
b. Guaranteed by design, not subject to production testing.

RATING AND CHARACTERISTIC CURVES

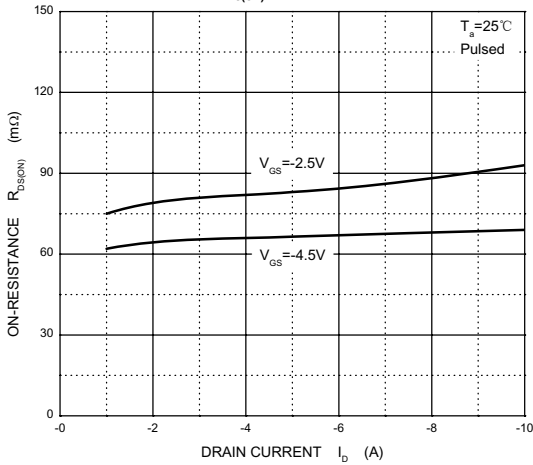
Output Characteristics



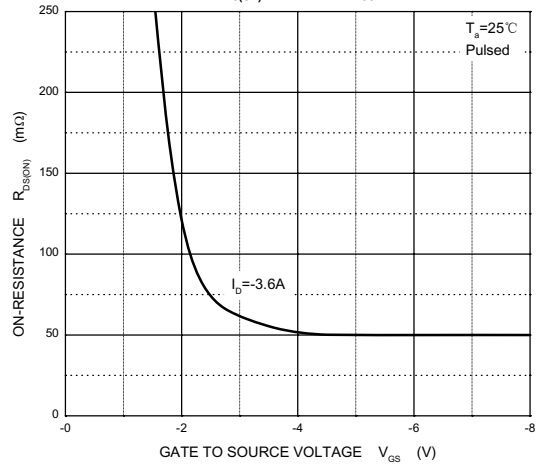
Transfer Characteristics



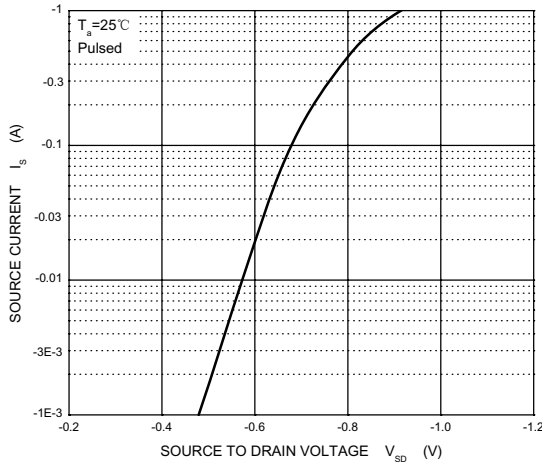
$R_{DS(ON)}$ — I_D



$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}



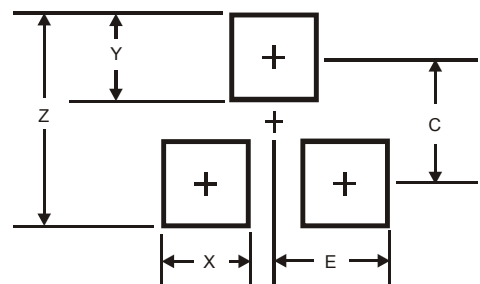
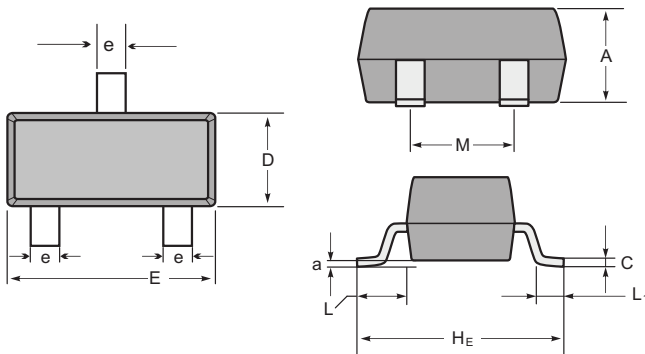
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



Package Dimensions & Suggested Pad Layout

SOT23

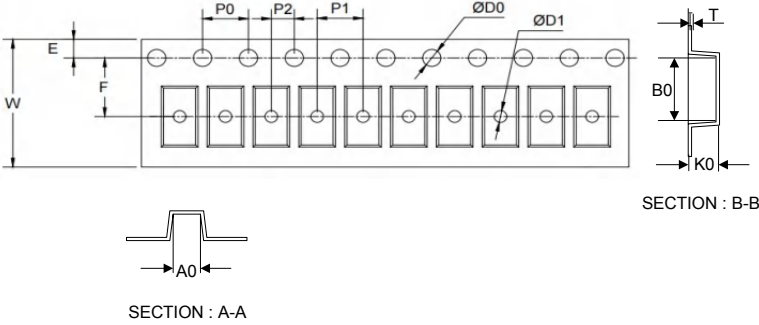


SOT-23 mechanical data

UNIT	A	C	D	E	HE	e	M	L	L1	a	
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Tape & reel specification

Tape	Symbol	Dimension (mm)
	P0	4.00±0.10
	P1	4.00±0.10
	P2	2.00±0.10
	D0	1.55±0.10
	D1	1.05±0.10
	E	1.55±0.10
	F	3.60±0.10
	W	8.00±0.10
	A0	3.80±0.20
	B0	3.25±0.20
7" Reel	K0	1.45±0.10
	T	0.25±0.05
	D2	178.0±3.0
	D3	55Min.
	D4	R24.0±3.0
	G	R82.0±3.0
	I	13.0±2.0
	W1	11.0±3.0
	Quantity: 3000PCS	